

METHOD TO FORM ULTRA HIGH QUALITY SILICON-CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown

Atty Docket: ASMEX.376A

1 / 13

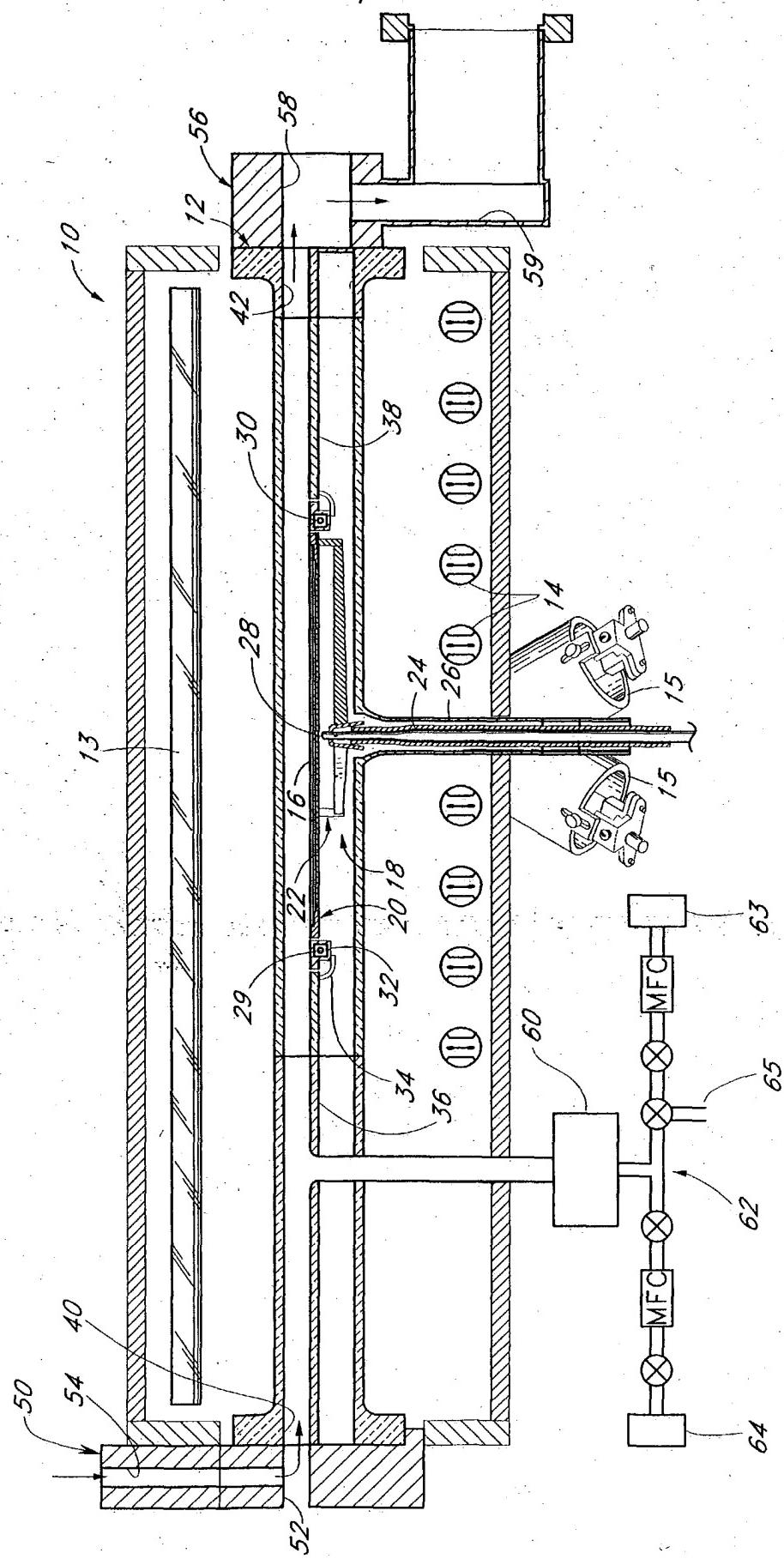


FIG. 1

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown Atty Docket: ASMEX.376A

2/13

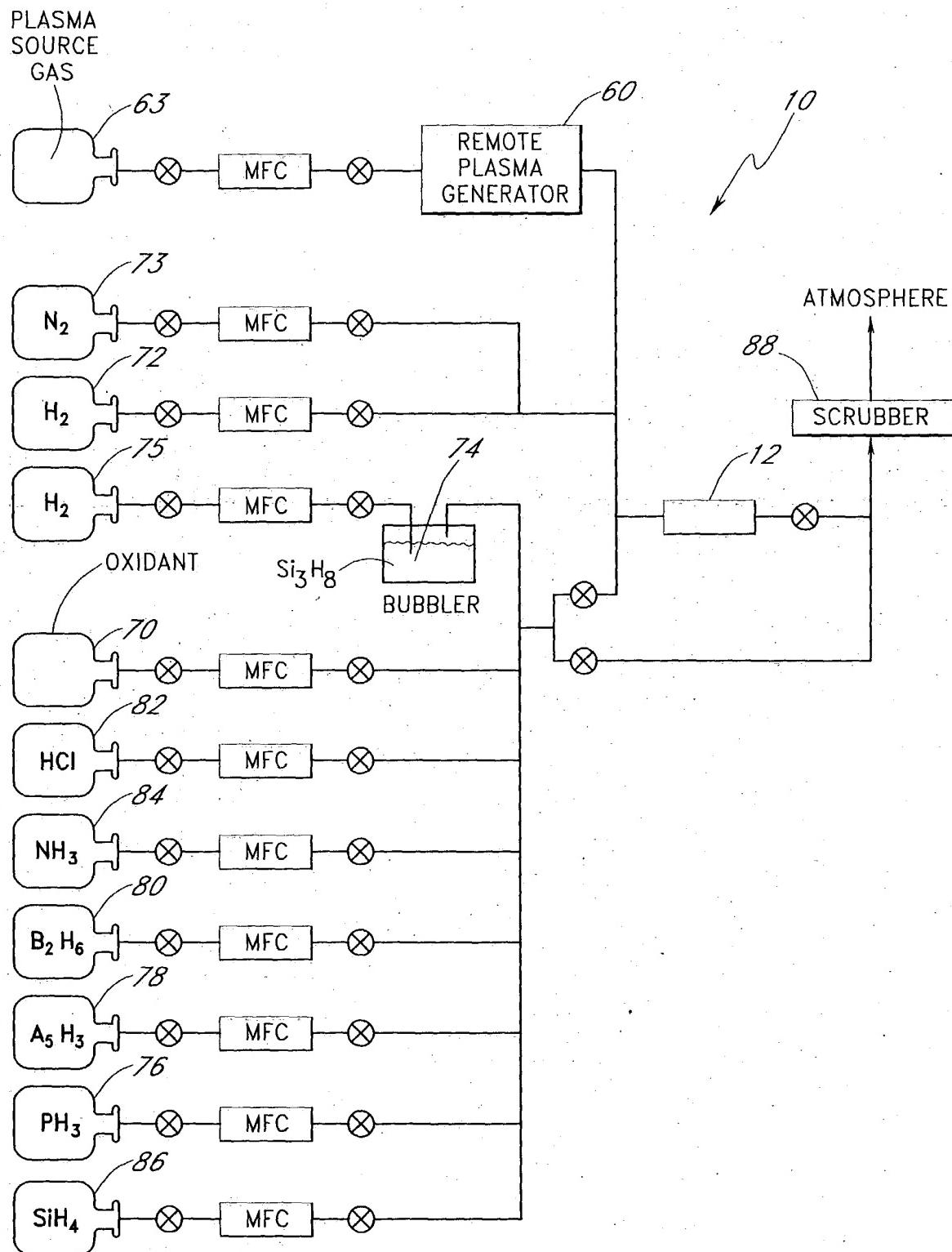


FIG. 2

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown

Atty Docket: ASMEX.376A

3/13

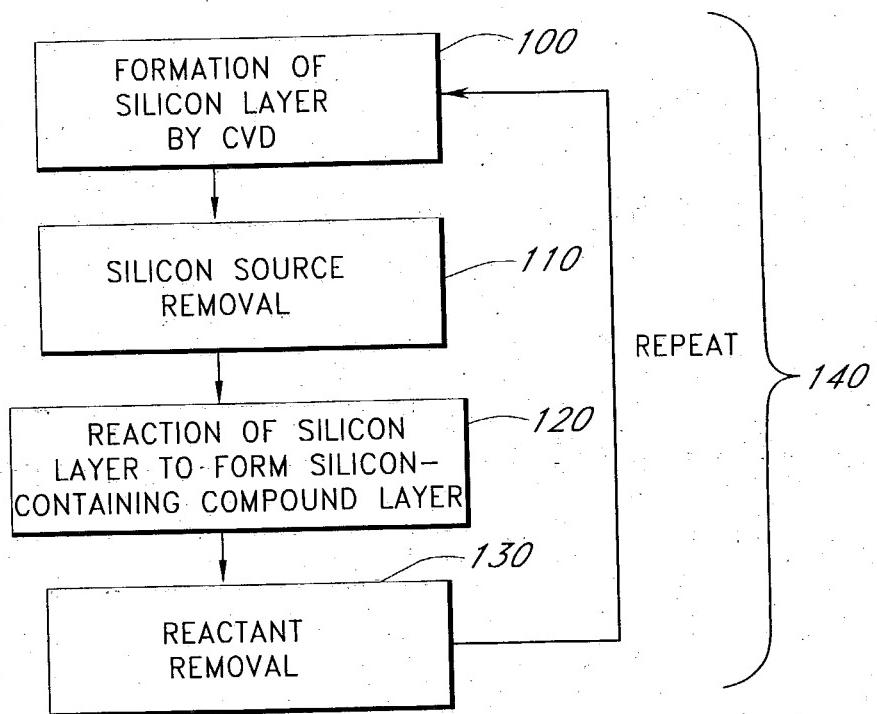


FIG. 3

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown

Atty Docket: ASMEX.376A

4/13

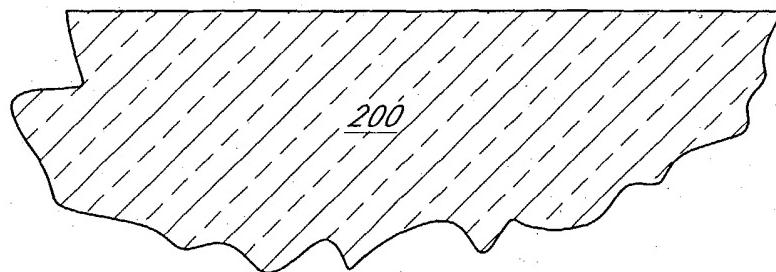


FIG. 4A

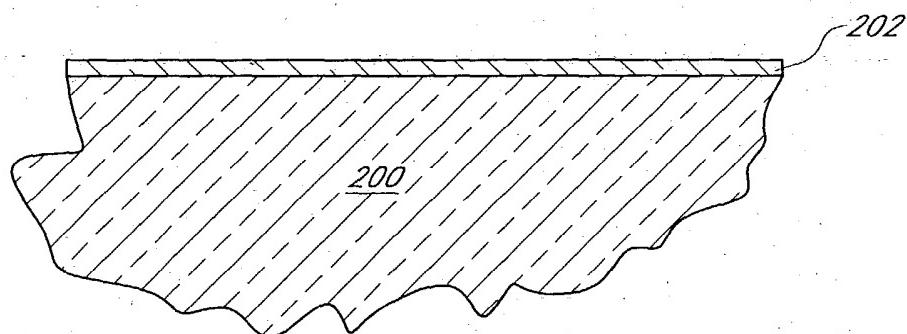


FIG. 4B

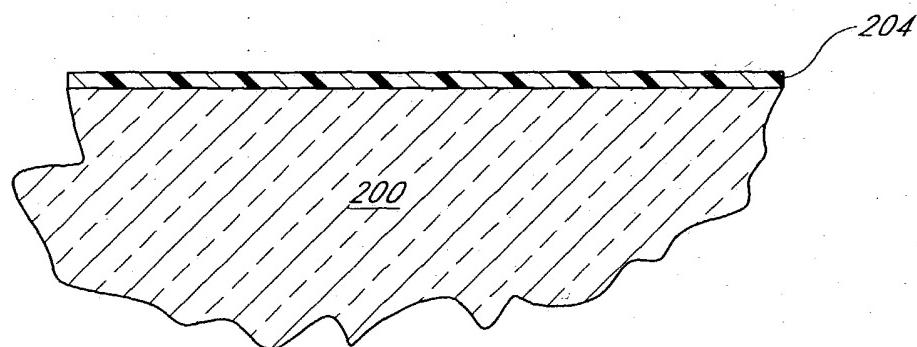


FIG. 4C

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS
Todd et al.
Appl. No.: Unknown Atty Docket: ASMEX.376A

5/13

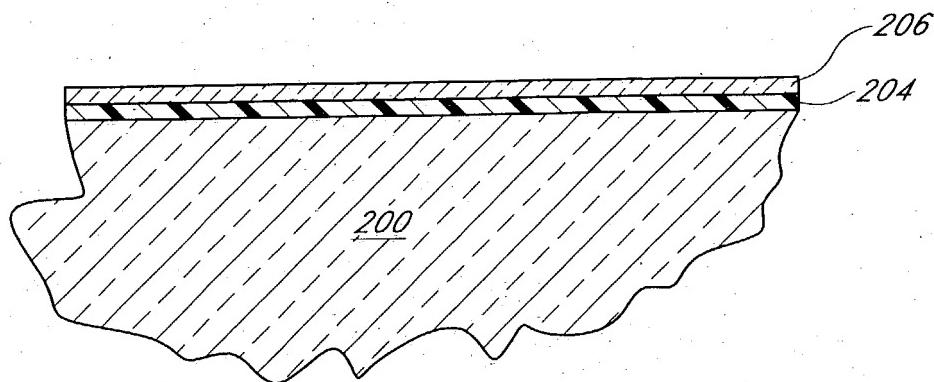


FIG. 4D

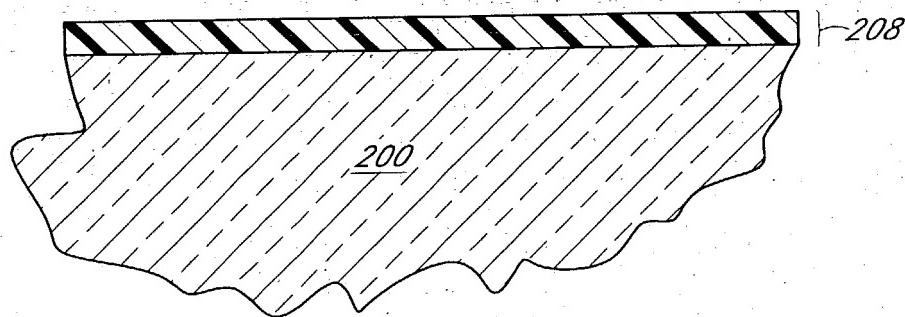


FIG. 4E

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS
Todd et al.

Appl. No.: Unknown Atty Docket: ASMEX.376A

6/13

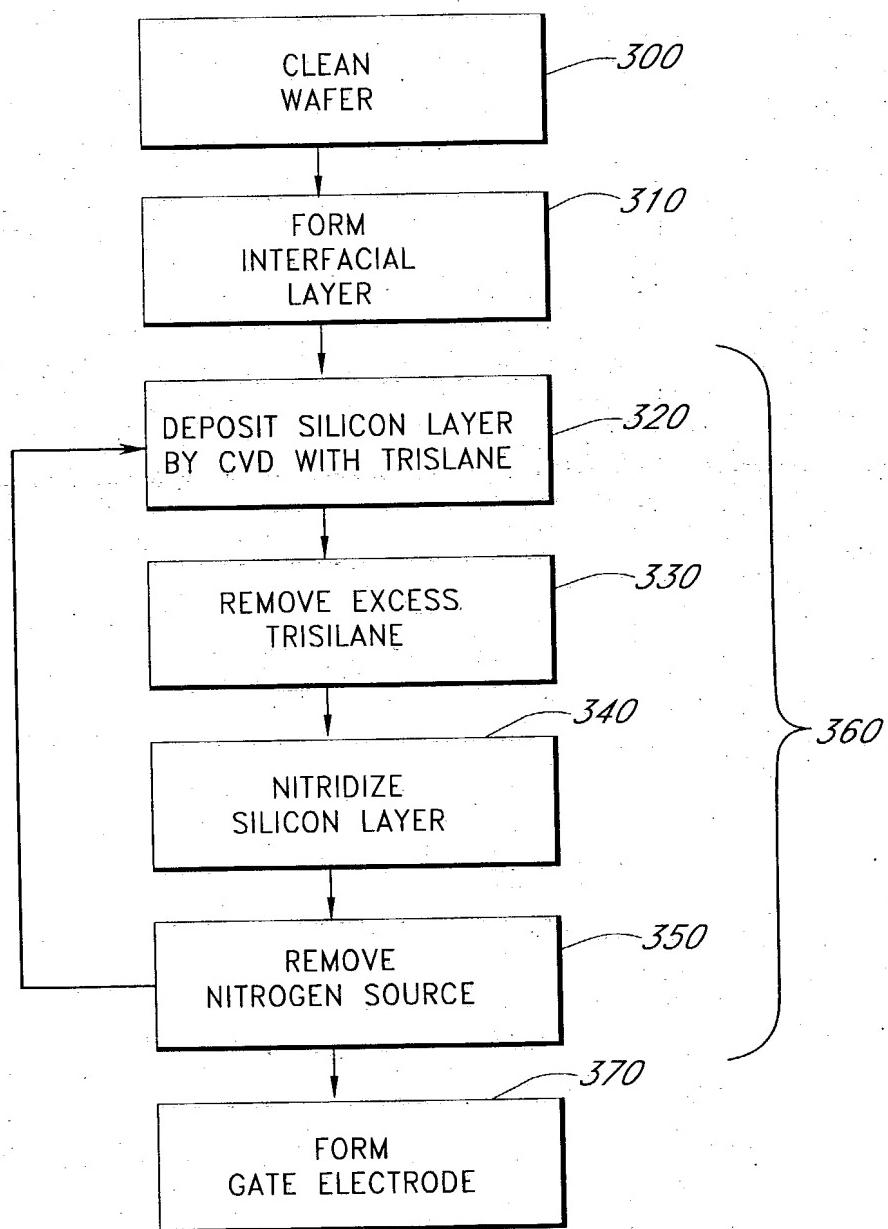


FIG.5

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown Atty Docket: ASMEX.376A

7/13

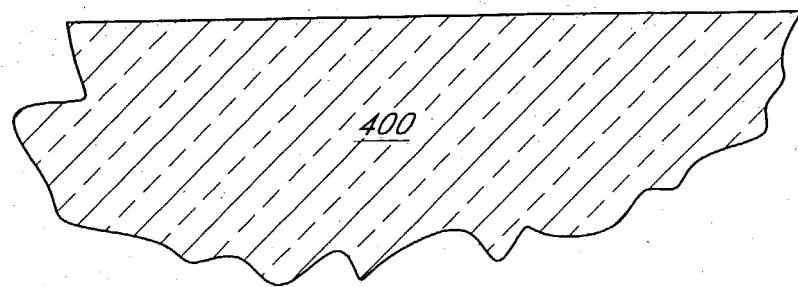


FIG. 6A

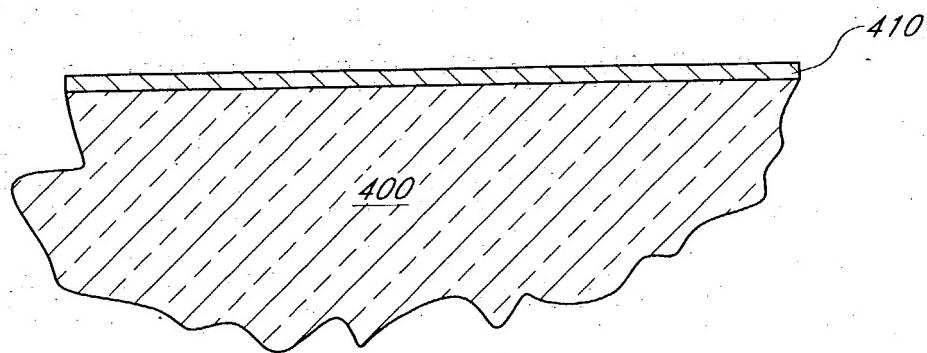


FIG. 6B

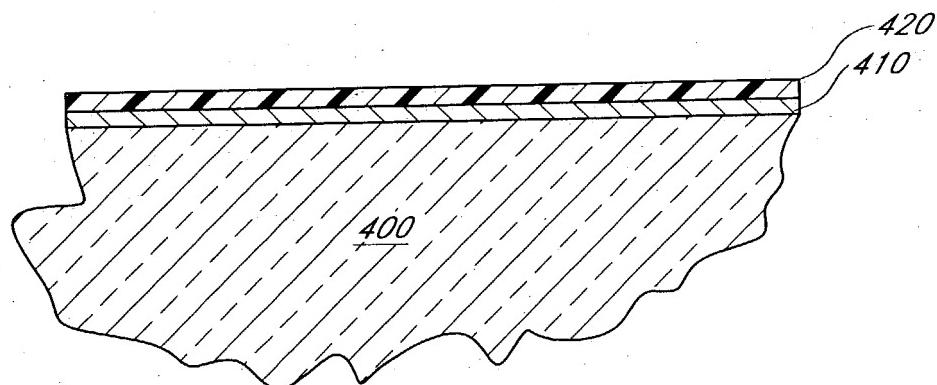


FIG. 6C

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown Atty Docket: ASMEX.376A

8/13

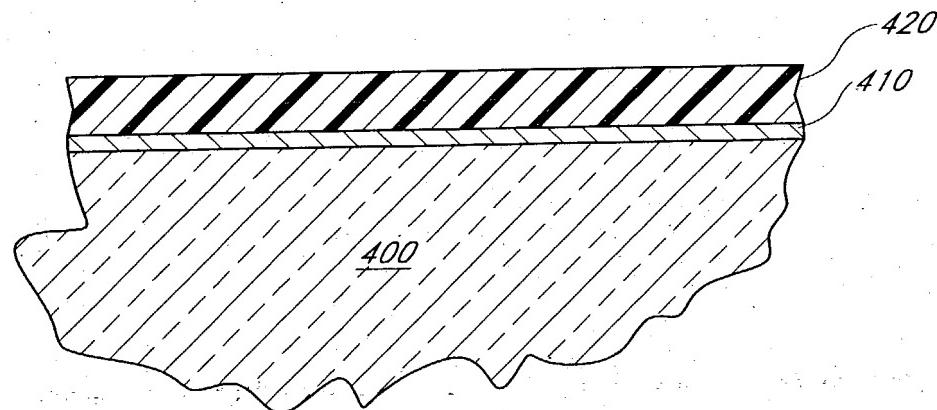


FIG. 6D

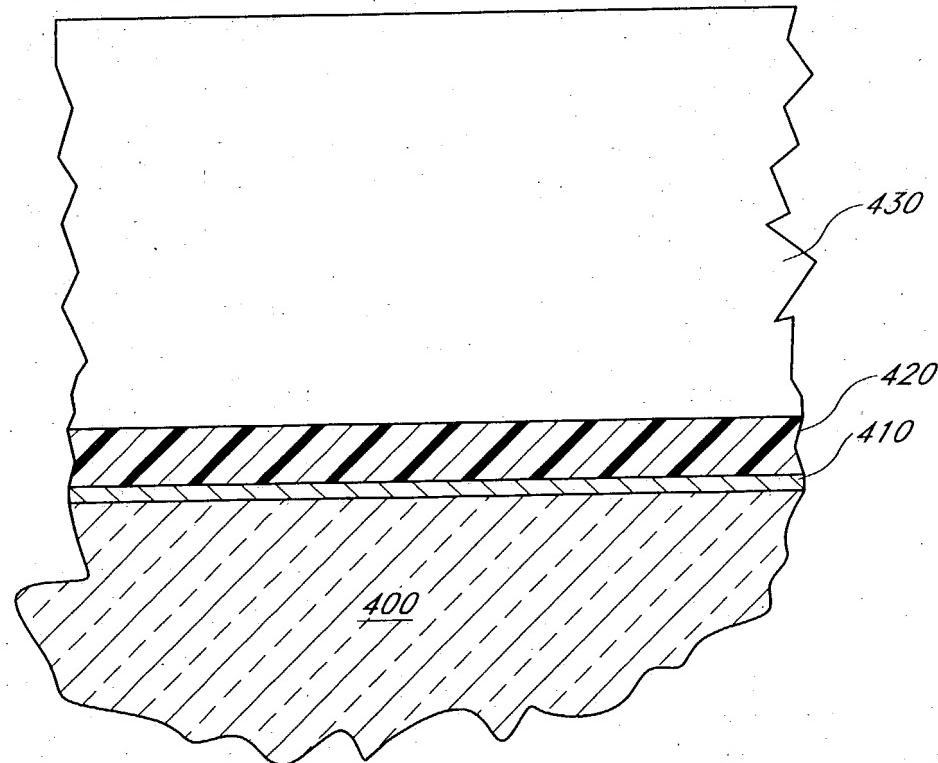


FIG. 6E

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.
Appl. No.: Unknown Atty Docket: ASMEX.376A

9/13

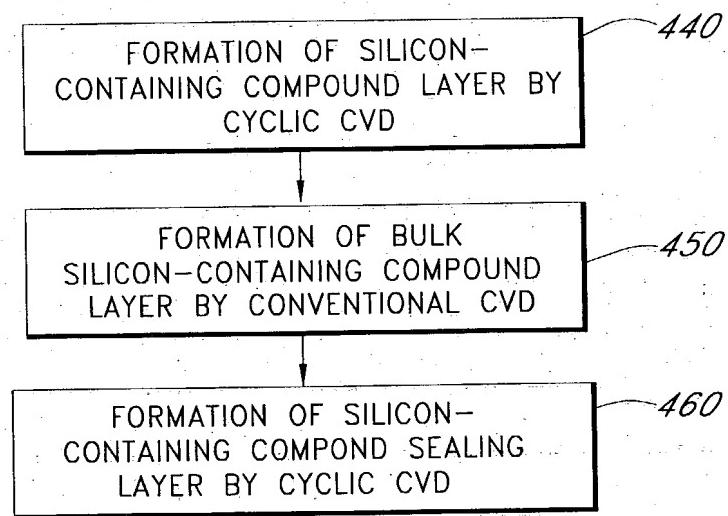


FIG. 7

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS

Todd et al.

Appl. No.: Unknown Atty Docket: ASMEX.376A

10/13

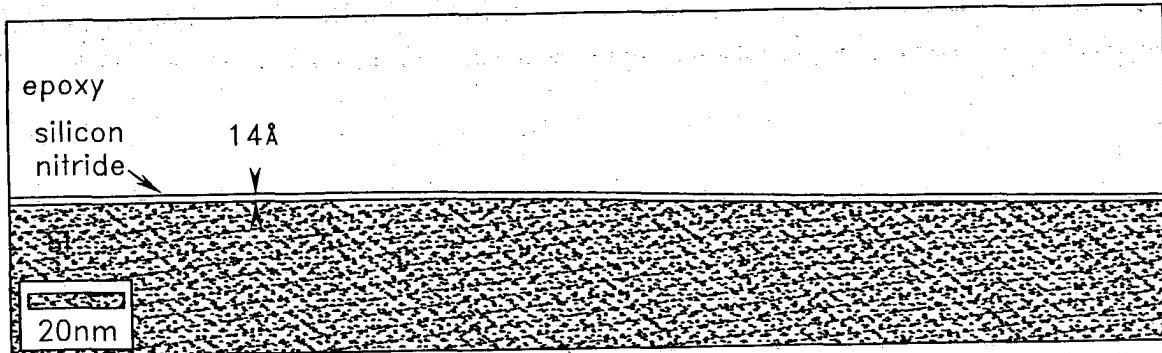


FIG. 8

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS
Todd et al.
Appl. No.: Unknown Atty Docket: ASMEX.376A

11/13

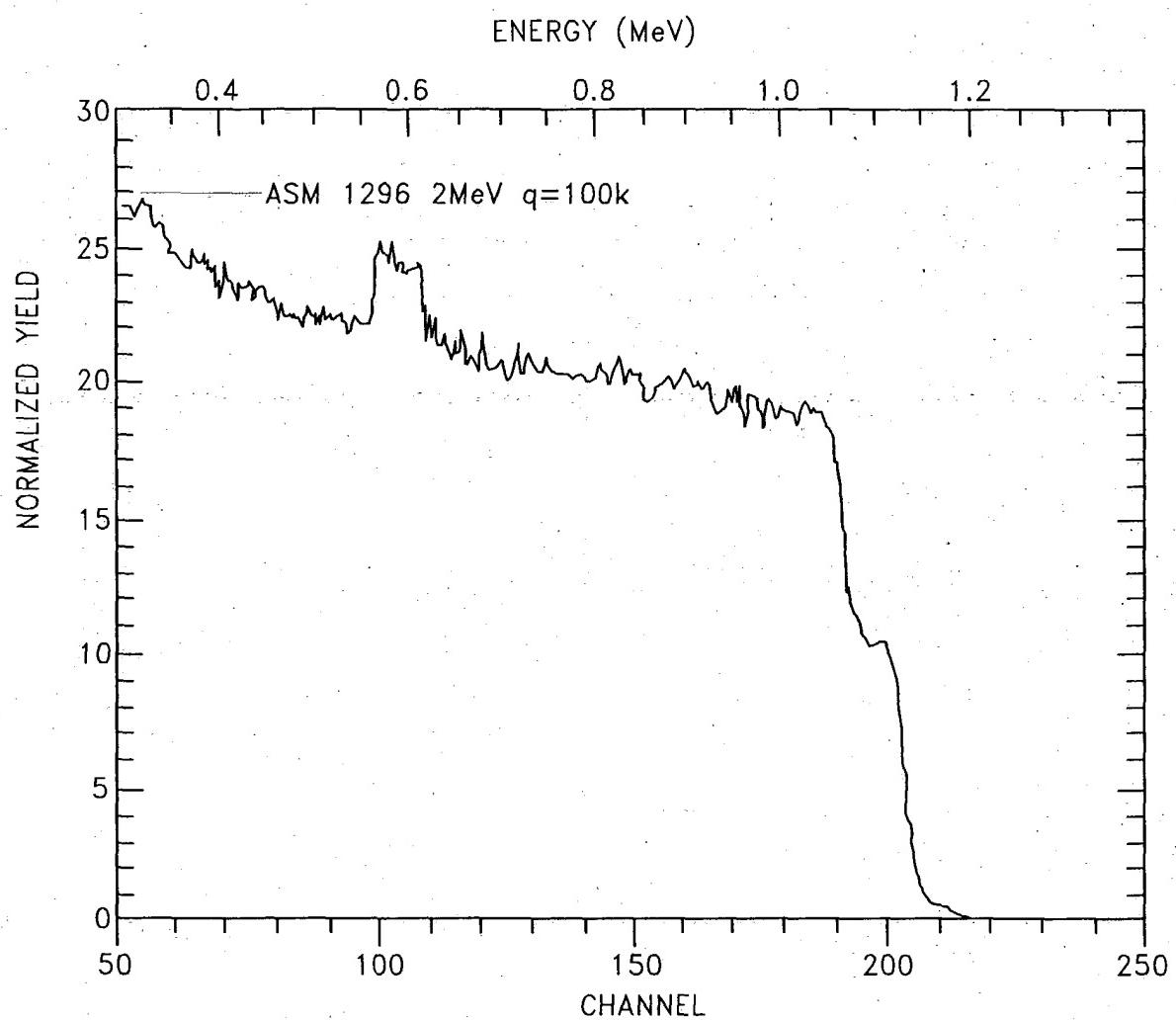


FIG. 9

METHOD TO FORM ULTRA HIGH QUALITY SILICON-
CONTAINING COMPOUND LAYERS
Todd et al.
Appl. No.: Unknown Atty Docket: ASMEX.376A

Todd et al.

Appl. No.: Unknown

Atty Docket: ASMEX.376A

12/13

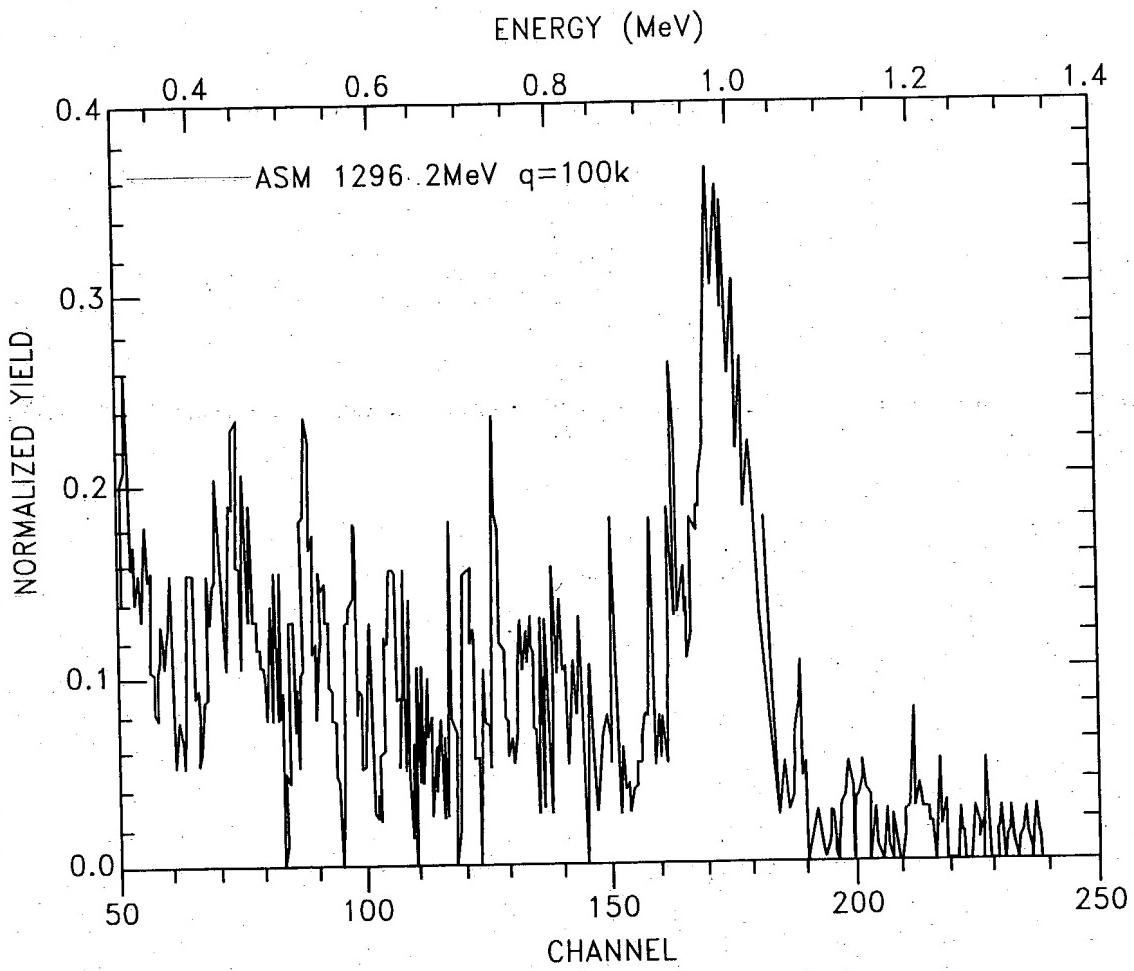


FIG. 10

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Todd et al.

Appl. No.: Unknown

Atty Docket: ASMEX.376A

13/13

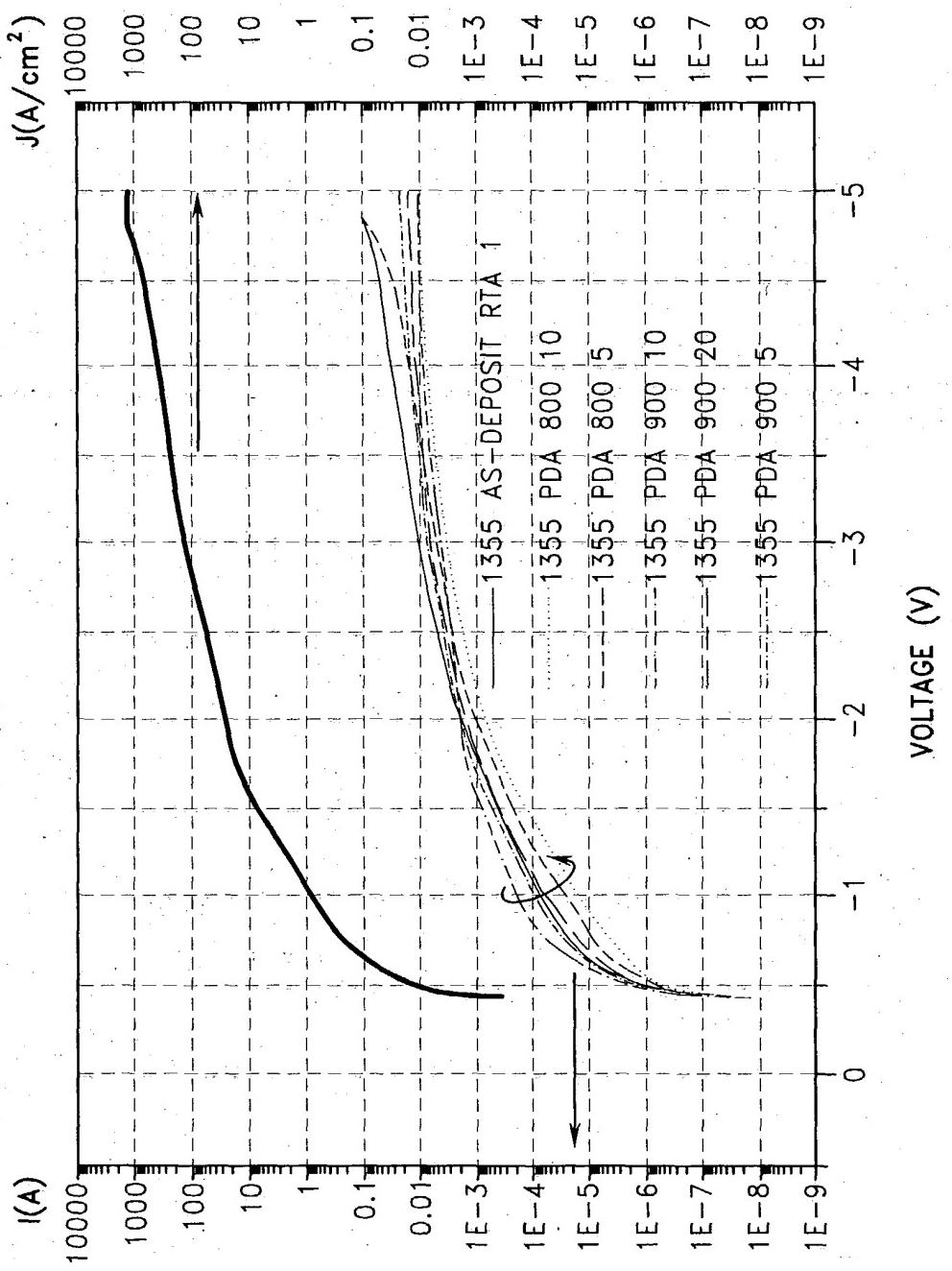


FIG. 11